

4. (Amended) The differential response light-receiving device according to claim 3, wherein said semiconductor is a metal oxide selected from the group consisting of TiO_2 , ZnO , SnO_2 and WO_3 .

5. (Amended) The differential response light-receiving device according to claim 2, wherein said differential response light-receiving device comprises a plurality of semiconductor electrodes, photosensitive wavelengths of said plurality of semiconductor electrodes being different from each other, and said ion-conductive electrolyte layer is disposed between said plurality of semiconductor electrodes and said counter electrode.

6. (Amended) The differential response light-receiving device according to claim 5, wherein said plurality of semiconductor electrodes are arranged in such order that said photosensitive wavelengths are increasing from light incident side of said differential response-type light-receiving device.

7. (Amended) The differential response light-receiving device according to claim 6, wherein said plurality of semiconductor electrodes comprises a blue-sensitive semiconductor electrode, a green-sensitive semiconductor electrode and a red-sensitive semiconductor electrode arranged in this order from said light incident side of said differential response light-receiving device.

8. (Amended) A composite light-receiving device comprising the differential response light-receiving device recited in claim 1 and a stationary response light-receiving device, said differential response light-receiving device and said stationary response-light-receiving device being arranged horizontally to said light-receiving surface or said differential response light-receiving device being stacked on said stationary response light-receiving device in the direction of light incidence.

9. (Amended) The composite light-receiving device according to claim 8, wherein said differential response light-receiving device and said stationary response light-receiving device are stacked.

10. (Amended) The composite light-receiving device according to claim 8, wherein said stationary response light-receiving device comprises: a semiconductor electrode comprising an electrically conductive layer and a photosensitive layer containing a semiconductor sensitized

by a dye; a charge transfer layer comprising a hole-transporting material or an electrolyte composition containing redox species; and a counter electrode.

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11. (Amended) The composite light-receiving device according to claim 10, wherein said semiconductor within said stationary response light-receiving device is a metal chalcogenide.

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12. (Amended) The composite light-receiving device according to claim 11, wherein said semiconductor within said stationary response light-receiving device is a metal oxide selected from the group consisting of TiO_2 , ZnO , SnO_2 and WO_3 .

13. (Amended) The composite light-receiving device according to claim 10, wherein said stationary response light-receiving device comprises a plurality of semiconductor electrodes, photosensitive wavelengths of said plurality of semiconductor electrodes being different from each other, and said charge transfer layer is disposed between said plurality of semiconductor electrodes and said counter electrode.

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16. (Amended) An image sensor comprising a plurality of pixels, wherein each of said pixels comprises the differential response light-receiving device recited in claim 1.